



ABSTRACT OF THE DISCLOSURE

~~The present invention provides a step in which a A channel-length of a TFT can~~
~~be controlled with higher reproducibility. In addition, the present invention provides a~~
~~step in which reproducibility, and a short channel-length of the TFT can be~~
~~manufactured. Further, the present invention provides a structure of the TFT in which a~~
~~having an improved current-voltage characteristic can be improved is provided. The~~
~~present invention refers to a A thin film transistor ~~comprising~~ has a lamination layer~~
~~wherein where a first conductive film, a first insulating film and a second conductive film~~
~~are sequentially laminated, a semiconductor film is formed so as to be in contact with~~
~~the side surface of the lamination layer, and a third conductive film ~~covering~~ covers the~~
~~semiconductor film through a second insulating film. The first conductive film and the~~
~~second conductive film are a source electrode and a drain electrode, ~~[[and]]~~ a region~~
~~which is in contact with the first insulating film and the third conductive film is a channel~~
~~forming region in the semiconductor film, and the third conductive film is a gate~~
~~electrode.~~